WHAT IS CLAIMED IS:

1. A light emitting device comprising:

a pixel portion;

a switching thin film transistor in the pixel portion;

a current control thin film transistor in the pixel portion;

at least an EL element electrically connected to the current control thin film transistor in the pixel portion;

wherein the switching thin film transistor is an n-channel thin film transistor;

wherein the current control thin film transistor is a p-channel thin film transistor;

a first pixel including a first EL element for emitting a red light in the pixel portion;

a second pixel including a second EL element for emitting a green light in the pixel portion;

a third pixel including a third EL element for emitting a blue light in the pixel portion;

wherein a triplet compound is used in the first EL element while a singlet compound is used in each of the second and third EL elements.

2. A light emitting device comprising:

a pixel portion;

a switching thin film transistor in the pixel portion;

a current control thin film transistor in the pixel portion;

at least an EL element electrically connected to the current control thin film transistor in the pixel portion;

wherein the switching thin film transistor is a p-channel thin film transistor;

wherein the current control thin film transistor is an n-channel thin film transistor;

a first pixel including a first EL element for emitting a red light in the pixel portion;

a second pixel including a second EL element for emitting a green light in the pixel portion;

a third pixel including a third EL element for emitting a blue light in the pixel portion;

wherein a triplet compound is used in the first EL element while a singlet compound is used in each of the second and third EL elements.

3. A light emitting device comprising:

a pixel portion;

a switching thin film transistor in the pixel portion;

a current control thin film transistor in the pixel portion;

at least an EL element electrically connected to the current control thin film transistor in the pixel portion;

wherein the switching thin film transistor is an n-channel thin film transistor;

wherein the current control thin film transistor is an n-channel thin film transistor;

a first pixel including a first EL element for emitting a red light in the pixel portion;

a second pixel including a second EL element for emitting a green light in the pixel portion;

a third pixel including a third EL element for emitting a blue light in the pixel portion;

wherein a triplet compound is used in the first EL element while a singlet compound is used in each of the second and third EL elements.

4. A light emitting device comprising:

a pixel portion;

a switching thin film transistor in the pixel portion;

a current control thin film transistor in the pixel portion;

at least an EL element electrically connected to the current control thin film transistor in the pixel portion;

wherein the switching thin film transistor is a p-channel thin film transistor;

wherein the current control thin film transistor is a p-channel thin film transistor;

a first pixel including a first EL element for emitting a red light in the pixel portion;

a second pixel including a second EL element for emitting a green

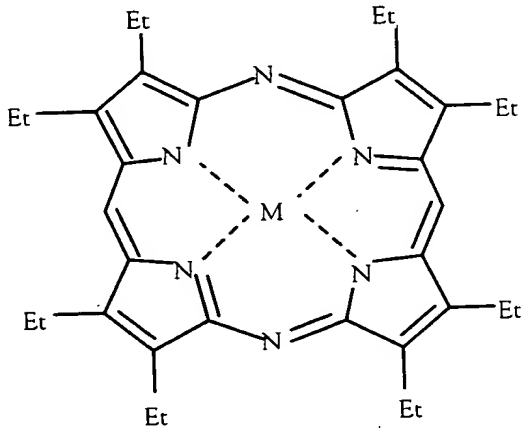
light in the pixel portion;

a third pixel including a third EL element for emitting a blue light in the pixel portion;

wherein a triplet compound is used in the first EL element while a singlet compound is used in each of the second and third EL elements.

5. A device according to claim 1,

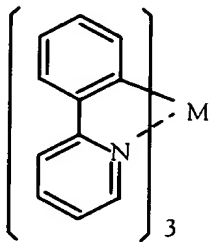
wherein the triplet compound is represented by



Et: ETHYL GROUP
M: ELEMENT BELONGING TO GROUPS 8-10 IN THE PERIODIC TABLE

6. A device according to claim 1,

wherein the triplet compound is represented by



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7. A device according to claim 5,

wherein the element belonging to Groups 8-10 in the periodic table is one selected from the group consisting of platinum, iridium, nickel, cobalt and palladium.

8. A device according to claim 1,

wherein each of the switching thin film transistor and the current control thin film transistor is a bottom gate thin film transistor.

9. A device according to claim 1,

wherein each of the switching thin film transistor and the current control thin film transistor is an inverted stagger thin film transistor.

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10. A module using the light emitting device of claim 1.

11. An electrical apparatus using the light emitting device of claim 1.

12. A portable telephone using the light emitting device of claim 1.

13. A digital camera using the light emitting device of claim 1.

14. An audio equipment using the light emitting device of claim 1.

15. A method of operating the EL element of claim 1 in a range of 10V or less.

16. A method of operating the EL element of claim 2 in a range of 10V or less.

17. A method of operating the EL element of claim 3 in a range of 10V or less.

18. A method of operating the EL element of claim 4 in a range of 10V or less.

19. A device according to claim 6,

wherein the element belonging to Groups 8-10 in the periodic table

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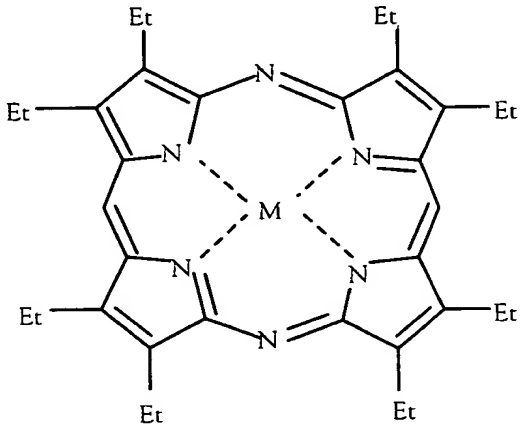
is one selected from the group consisting of platinum, iridium, nickel, cobalt and palladium.

20. A device according to claim 2,

wherein the triplet compound is represented by



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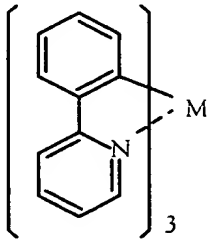
21. A device according to claim 2,

wherein the triplet compound is represented by



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22. A device according to claim 20,

wherein the element belonging to Groups 8-10 in the periodic table is one selected from the group consisting of platinum, iridium, nickel, cobalt and palladium.

23. A device according to claim 21,

wherein the element belonging to Groups 8-10 in the periodic table is one selected from the group consisting of platinum, iridium, nickel, cobalt and palladium.

24. A device according to claim 2,

wherein each of the switching thin film transistor and the current control thin film transistor is a bottom gate thin film transistor.

25. A device according to claim 2,

wherein each of the switching thin film transistor and the current control thin film transistor is an inverted stagger thin film transistor.

26. A module using the light emitting device of claim 2.

27. An electrical apparatus using the light emitting device of claim 2.

28. A portable telephone using the light emitting device of claim 2.

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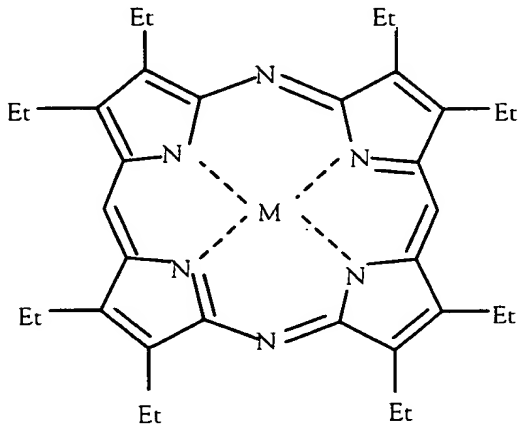
29. A digital camera using the light emitting device of claim 2.

30. An audio equipment using the light emitting device of claim 2.

31. A device according to claim 3,

wherein the triplet compound is represented by



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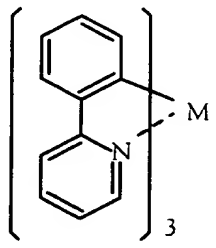
32. A device according to claim 3,

wherein the triplet compound is represented by



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33. A device according to claim 31,

wherein the element belonging to Groups 8-10 in the periodic table is one selected from the group consisting of platinum, iridium, nickel, cobalt and palladium.

34. A device according to claim 32,

wherein the element belonging to Groups 8-10 in the periodic table is one selected from the group consisting of platinum, iridium, nickel, cobalt and palladium.

35. A device according to claim 3,

wherein each of the switching thin film transistor and the current control thin film transistor is a bottom gate thin film transistor.

36. A device according to claim 3,

wherein each of the switching thin film transistor and the current control thin film transistor is an inverted stagger thin film transistor.

37. A module using the light emitting device of claim 3.

38. An electrical apparatus using the light emitting device of claim 3.

39. A portable telephone using the light emitting device of claim 3.

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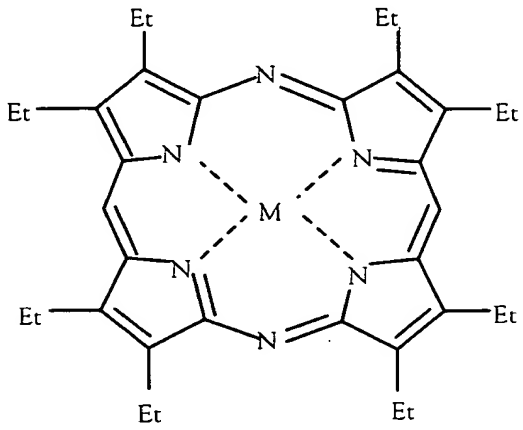
40. A digital camera using the light emitting device of claim 3.

41. An audio equipment using the light emitting device of claim 3.

42. A device according to claim 4,

wherein the triplet compound is represented by



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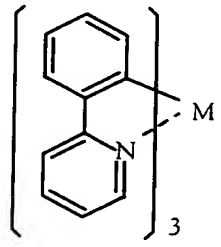
43. A device according to claim 4,

wherein the triplet compound is represented by



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44. A device according to claim 42,

wherein the element belonging to Groups 8-10 in the periodic table is one selected from the group consisting of platinum, iridium, nickel, cobalt and palladium.

45. A device according to claim 43,

wherein the element belonging to Groups 8-10 in the periodic table is one selected from the group consisting of platinum, iridium, nickel, cobalt and palladium.

46. A device according to claim 4,

wherein each of the switching thin film transistor and the current control thin film transistor is a bottom gate thin film transistor.

47. A device according to claim 4,

wherein each of the switching thin film transistor and the current control thin film transistor is an inverted stagger thin film transistor.

48. A module using the light emitting device of claim 4.

49. An electrical apparatus using the light emitting device of claim 4.

50. A portable telephone using the light emitting device of claim 4.

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51. A digital camera using the light emitting device of claim 4.

52. An audio equipment using the light emitting device of claim 4.

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